



**SDI Review Form 1.6**

Journal Name:	<a href="#">Physical Science International Journal</a>
Manuscript Number:	2015_PSIJ_18553
Title of the Manuscript:	Electrical and photoelectric properties of crystal InGaTe2
Type of the Article	

**General guideline for Peer Review process:**

This journal's peer review policy states that **NO** manuscript should be rejected only on the basis of '**lack of Novelty**', provided the manuscript is scientifically robust and technically sound.

To know the complete guideline for Peer Review process, reviewers are requested to visit this link:

(<http://www.sciencedomain.org/page.php?id=sdi-general-editorial-policy#Peer-Review-Guideline>)



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**PART 1: Review Comments**

	Reviewer's comment	Author's comment (if agreed with reviewer, correct the manuscript and highlight that part in the manuscript. It is mandatory that authors should write his/her feedback here)
<b><u>Compulsory</u></b> REVISION comments	<p>I have read the article carefully for several times and found it with some questions, such as the langue usages and some wrong words, it's only about the expression. For example, (1) "Found that acceptor centers are with the depth of 0.203 eV and 0801 eV". (2) " As is known, at higher degrees of optic excitation a sufficiently high 'consentration nonequilibrium'carrier..." ,and so on.</p> <p>On the whole, the article has accounted for the mechanism of optical absorption in InGaTe2 crystal, maybe it will make some sense to the InGaTe2 crystal in the photoconduction application field. If the author improves the langue expressions, it's worthy of publication.</p>	<p>There were some technical mistakes that we corrected in the text. For example , 0801eV replaced 0.801eV and so on. Language mistakes also have been corrected.</p>
<b><u>Minor</u></b> REVISION comments		
<b><u>Optional/General</u></b> comments		